# 2SD2121(L)/(S)

Silicon NPN Epitaxial

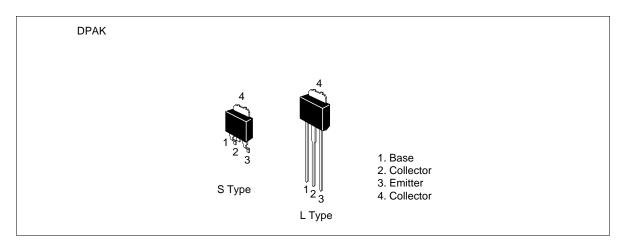
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ADE-208-925 (Z) 1st. Edition Sep. 2000

### **Application**

Low frequency power amplifier complementary pair with 2SB1407(L)/(S)

#### **Outline**



## **Absolute Maximum Ratings** (Ta = 25°C)

Item	Symbol	Ratings	Unit
Collector to base voltage	$V_{\text{CBO}}$	35	V
Collector to emitter voltage	$V_{\text{CEO}}$	35	V
Emitter to base voltage	$V_{EBO}$	5	V
Collector current	I <sub>c</sub>	2.5	A
Collector peak current	I <sub>C(peak)</sub>	3	A
Collector power dissipation	P <sub>c</sub> *1	18	W
Junction temperature	Tj	150	°C
Storage temperature	Tstg	-55 to +150	°C

Note: 1. Value at  $T_c = 25$ °C.



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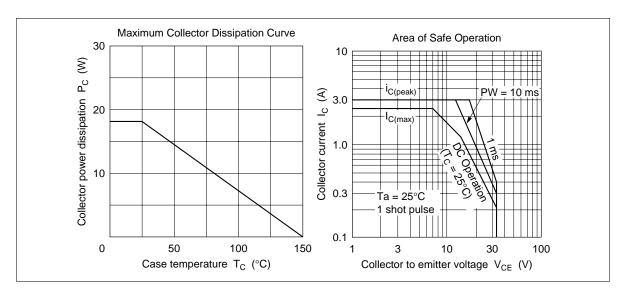
## **Electrical Characteristics** (Ta = 25°C)

Item	Symbol	Min	Тур	Max	Unit	Test conditions
Collector to base breakdown voltage	$V_{(BR)CBO}$	35	_	_	V	$I_{c} = 1 \text{ mA}, I_{E} = 0$
Collector to emitter breakdown voltage	$V_{(BR)CEO}$	35	_	_	V	$I_{c}$ = 10 mA, $R_{BE}$ = $\infty$
Emitter to base breakdown voltage	$V_{(BR)EBO}$	5	_	_	V	$I_E = 1 \text{ mA}, I_C = 0$
Collector cutoff current	I <sub>CBO</sub>	_	_	20	μΑ	$V_{CB} = 35 \text{ V}, I_{E} = 0$
DC current transfer ratio	h <sub>FE1</sub> *1	60	_	320		$V_{CE} = 2 \text{ V}, I_{C} = 0.5 \text{ A}^{*2}$
	h <sub>FE2</sub>	20	_	_		$V_{CE} = 2 \text{ V}, I_{C} = 1.5 \text{ A}^{*2}$
Base to emitter voltage	$V_{\text{BE}}$	_	_	1.5	V	$V_{CE} = 2 \text{ V}, I_{C} = 1.5 \text{ A}^{*2}$
Collector to emitter saturation voltage	$V_{\text{CE(sat)}}$	_	_	1.0	V	$I_{\rm C} = 2 \text{ A}, I_{\rm B} = 0.2 \text{ A}^{*2}$

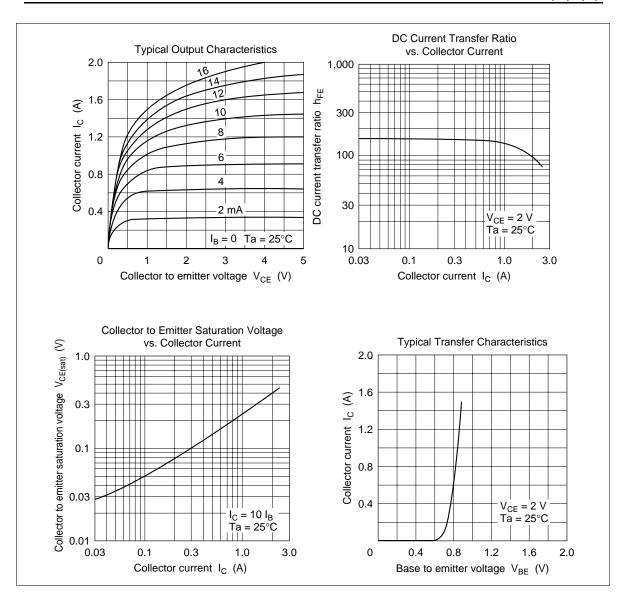
Notes: 1. The 2SD2121(L)/(S) is grouped by  $h_{FE1}$  as follows.

В	С	D
60 to 120	100 to 200	160 to 320

#### 2. Pulse test.

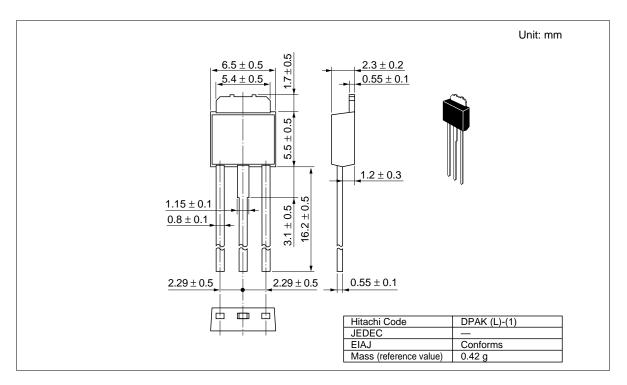


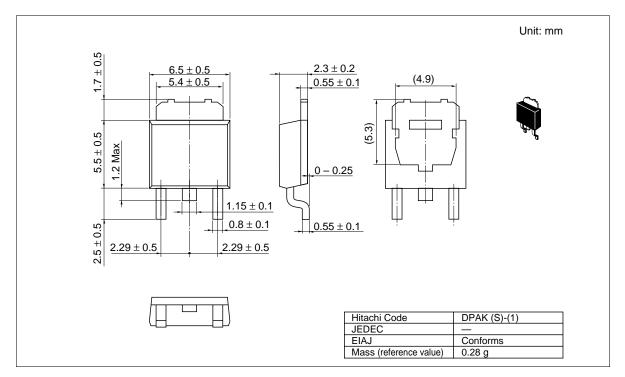
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## 2SD2121(L)/(S)

### **Package Dimensions**





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#### **Cautions**

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